



PST KP4301

HIGH POWER PHASE CONTROL THYRISTOR FOR PHASE CONTROL APPLICATIONS

Features :

- Blocking Capability up to 2200 V
- High dV/dt Capability
- All Diffused Structure
- Amplifying Gate Configuration
- Rugged Ceramic Hermetic Package

ELECTRICAL CHARACTERISTICS AND RATINGS

Blocking

Parameter	Symbol	Min	Max	Typ	Unit	Conditions
Repetitive peak reverse voltage	V_{RRM}		2200		V	$T_j = -40^\circ C$ to $125^\circ C$
Repetitive peak off-state voltage	V_{DRM}		2200		V	$T_j = -40^\circ C$ to $125^\circ C$
Non repetitive peak reverse voltage	V_{RSM}		2300		V	$T_j = -40^\circ C$ to $125^\circ C$
Repetitive peak reverse current	I_{RRM}		300		mA	$T_j = T_{jmax}$, $V = V_{RRM}$
Repetitive peak off-state current	I_{DRM}		300		mA	$T_j = T_{jmax}$, $V = V_{DRM}$

Conducting

Parameter	Symbol	Min	Max	Typ	Unit	Conditions
Average value of on-state current	$I_{T(AV)}$		4030		A	50 Hz sine wave, 180° conduction, $T_c = 85^\circ C$
RMS value of on-state current	$I_{T(RMS)}$		6330		A	50 Hz sine wave, 180° conduction, $T_c = 85^\circ C$
Surge non repetitive current	I_{TSM}		91		kA	50 Hz sine wave Half cycle
$I^2 t$	$I^2 t$		41405		kA ² s	$V_R = 0$ $T_j = T_{jmax}$
Peak on-state voltage	V_{TM}		1.2		V	On-state current 4000 A, $T_j = T_{jmax}$
Threshold voltage	$V_{T(TO)}$		0.77		V	$T_j = T_{jmax}$
On-state slope resistance	r_T		0.11		mΩ	$T_j = T_{jmax}$
Holding current	I_H			350	mA	$V_D = 12 V$; $I_T = 2.5 A$
Latching current	I_L			1000	mA	$V_D = 12 V$; $R_L = 12 \Omega$

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Triggering

Parameter	Symbol	Min	Max	Typ	Unit	Conditions
Gate current	I_{GT}		300		mA	$V_D = 6 \text{ V}; R_L = 3 \Omega; T_j = -40 \text{ }^\circ\text{C}$
			200		mA	$V_D = 6 \text{ V}; R_L = 3 \Omega; T_j = 25 \text{ }^\circ\text{C}$
			125		mA	$V_D = 6 \text{ V}; R_L = 3 \Omega; T_j = 125 \text{ }^\circ\text{C}$
Gate voltage	V_{GT}		5		V	$V_D = 6 \text{ V}; R_L = 3 \Omega; T_j = -40 \text{ }^\circ\text{C}$
			4		V	$V_D = 6 \text{ V}; R_L = 3 \Omega; T_j = 0 \div 125 \text{ }^\circ\text{C}$
		0.3			V	$V_D = V_{DRM}; R_L = 10 \text{ k}\Omega; T_j = 125 \text{ }^\circ\text{C}$
Peak gate current	I_{GM}		15		A	
Peak reverse gate voltage	V_{RGM}		15		V	
Peak gate power dissipation	P_{GM}		200		W	
Average gate power dissipation	$P_{G(AV)}$		5		W	

Switching

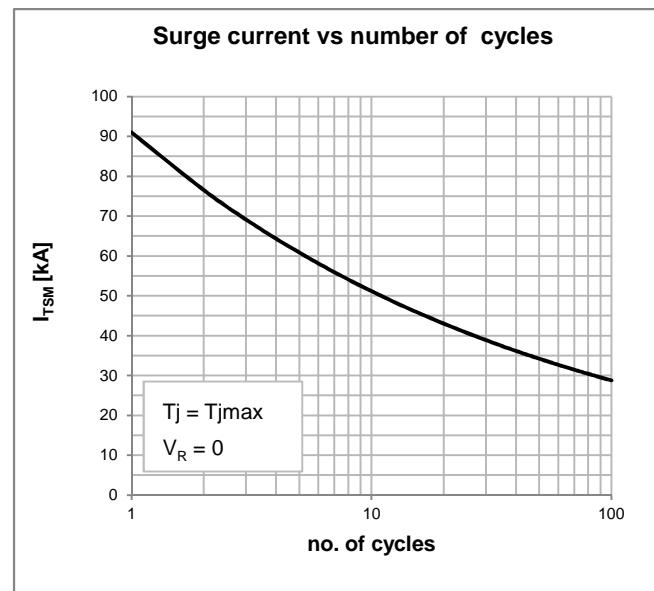
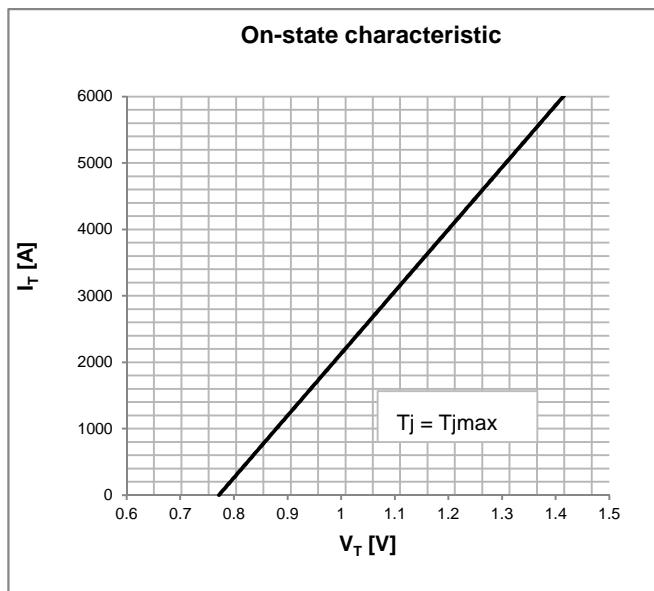
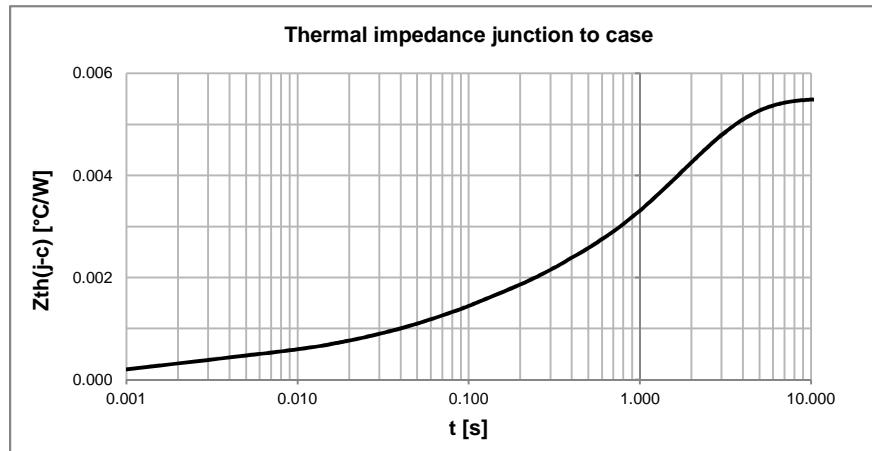
Parameter	Symbol	Min	Max	Typ	Unit	Conditions
Critical rate of rise of on-state current	di/dt		300		A/ μ s	$I_G = 5 \cdot I_{GT}, t_r = 1 \mu\text{s}, T_j = T_{jmax}$
Critical rate of rise of on-state voltage	dv/dt		1000		V/ μ s	Linear ramp up to 80% of V_{DRM}
Gate controlled delay time	t_d				μ s	$I_{TM} = 50 \text{ A}; V_D = 1500 \text{ V}; V_G = 20 \text{ V}$ $R_G = 20 \Omega; t_r = 0.1 \mu\text{s}; t_p = 20 \mu\text{s}$
Turn-off time	t_q			250	μ s	$I_{TM} = 4300 \text{ A}; di/dt = 10 \text{ A}/\mu\text{s}; V_R \geq 100 \text{ V}$ $dV/dt = 20 \text{ V}/\mu\text{s}$ linear to 67% V_{DRM} $V_G = 0 \text{ V}; T_j = T_{jmax}$
Reverse recovery charge	Q_{rr}				μ C	$I_T = 500 \text{ A}$ $di/dt = 20 \text{ A}/\mu\text{s}$
Reverse recovery current	I_{rr}				A/ μ s	$V_R \geq 50 \text{ V}$ $T_j = T_{jmax}$

Thermal and mechanical

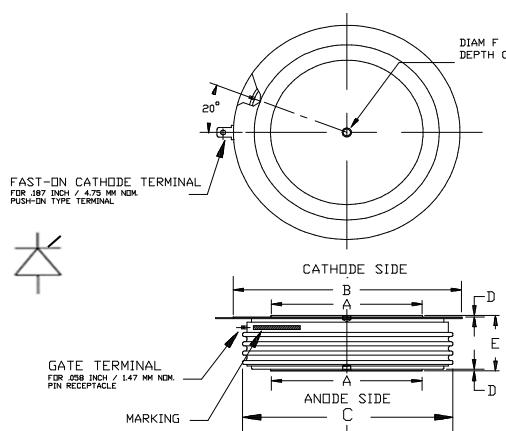
Parameter	Symbol	Min	Max	Typ	Unit	Conditions
Operating temperature	T_j	-40	125		$^\circ\text{C}$	
Storage temperature	T_{stg}	-40	150		$^\circ\text{C}$	
Thermal resistance junction to case	$R_{th(j-c)}$		0.0055		$^\circ\text{C}/\text{W}$	Double side cooled , 180° SIN
Thermal resistance case to sink	$R_{th(c-s)}$		0.0015		$^\circ\text{C}/\text{W}$	Double side cooled, mounting surfaces smooth, flat and greased
Mounting force	F	60	90		kN	
Weight	W			2800	g	

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OUTLINE AND DIMENSIONS



	A	B	C	E
mm	100	150	131	35+-1
inches	3.93	5.90	5.15	1.37

- All the characteristics given in this data sheet are guaranteed only with uniform clamping force, cleaned and lubricated heatsink surfaces with flatness < 0.03 mm and roughness < 2µm